

Docket No.: 60188-431

PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Application of

Akihiko ISHIBASHI, et al.

Serial No.: 10/017,389

Group Art Unit: 2818

Filed: December 18, 2001

Examiner: TRAN, MAI HUONG C.

For: METHOD FOR FABRICATING SEMICONDUCTOR, METHOD FOR
FABRICATING SEMICONDUCTOR SUBSTRATE, AND SEMICONDUCTOR
LIGHT EMITTING DEVICE

PRELIMINARY AMENDMENT

Mail Stop Preliminary Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Prior to examination of the above-referenced application, please amend the application as follows:

IN THE CLAIMS:

Please add new claims 14-17 as follows:

14. (New) The method of claim 1, wherein the first semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.

15. (New) The method of claim 4, wherein the semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.

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TECHNICAL STAFF